Ultra-low vibration closed-cycle cryogenic surface-electrode ion trap apparatus

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We describe the design, commissioning and operation of an ultra-low vibration closed-cycle cryogenic ion trap apparatus. 100 DC connection lines, 10 of which are suitable for currents up to 1 A, and eight microwave / rf coaxial feed lines offer the possibility of implementing a small-scale ion-trap quantum processor or simulator. With all supply cables attached, more than 1.3 W of cooling power at 5 K is still available for absorbing energy from electrical pulses introduced to control ions. The trap itself is protected from vibrations induced by the cold head using a helium exchange gas interface. The performance of the vibration isolation system has been characterized using a Michelson interferometer, finding residual vibration amplitudes on the order of 10 nm rms. Trapping of $^9$Be$^+$ ions has been demonstrated using a combination of laser ablation and photoionization.

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I. INTRODUCTION

Trapped atomic ions are an exceptionally well controlled quantum system with applications in scalable quantum logic, frequency metrology, quantum simulation, and other areas. While ground state cooling of the quantized motional degrees of freedom of trapped ions has been a key enabling step for applications, the traps themselves can be kept at room temperature. Nevertheless, moderate cryogenic cooling of the ion trap itself can represent an important advantage. In a cryogenic vacuum apparatus, the achievable pressures can be much lower than for room-temperature ultra-high vacuum systems, enabling long lifetimes of the trapped particles. This can be of particular importance in the case of small-scale micro-fabricated and surface-electrode traps used in the context of quantum logic and simulations, as they may exhibit relatively shallow potential well depths, making the ion(s) susceptible to loss from collisions with background gas atoms. Even before trap loss occurs, collisions could affect the motional state of the ion(s), which is detrimental in many applications. In frequency metrology, an important systematic effect, namely the black-body radiation shift of atomic clock transitions due to the finite temperature of the ion’s thermal environment, can be strongly suppressed by keeping the ion in a cryogenically cooled environment. Finally, an undesirable interaction between spurious fields emanating from the trap electrode materials and the ion(s) may excite the ions’ motion in an uncontrolled way. This effect, known as ‘anomalous motional heating’, can be an important systematic effect in ion clocks through uncontrolled Doppler shifts, and may affect the fidelity of multi-qubit quantum logic gates. This effect appears to be thermally activated and can thus be strongly suppressed by cooling the trap electrodes to moderate cryogenic temperatures.

A potential concern for cryogenic operation is the added experimental overhead. Compared to other quantum systems, however, which may be impossible to operate without deep cryogenic cooling to $\approx$ mK temperatures, ions already achieve the above advantages with moderate cooling to liquid helium temperatures. Another concern may be the consumption of liquid helium, in particular since many ion-trap applications require optical access for laser beams, which increases the heat load on the system and the liquid helium consumption. An obvious solution, the use of a closed-cycle refrigeration system, typically introduces issues due to mechanical vibrations from the cryo cooler itself, which can affect the performance of the system, in particular with respect to focused-laser beam interrogation and manipulation of the ion(s). In addition, a closed-cycle system typically exhibits a given cooling power which cannot be expanded by accepting a higher cryogen boil-off per unit time. This requires a careful design of the vacuum system and cryogenic shields to minimize the effect of thermal radiation and of the electrical connection system because of the potential introduction of heat through these connections.

Here we present a cryogenic ion trap apparatus for surface-electrode ion traps based on a closed-cycle refrigeration system with minimal mechanical vibrations. We describe the experiment concept and the surface-electrode trap. We discuss the electrical connection system, comprising DC, RF and microwave control signals, the vacuum system, vibration isolation system, laser sources and imaging system and finally show successful trapping of $^9$Be$^+$ ions.

II. CONCEPT

A. Design goals

The application scenario of the setup discussed here is for scalable quantum logic and simulations with trapped
ions using near-field microwaves for the underlying multi-qubit interactions. The microwave near-fields are generated by currents in trap-embedded conductors directly addressing a field-independent hyperfine qubit in $^9$Be$^+$. Design, characterization, two-qubit gates, and high-fidelity operation have been shown for a room temperature setup. Present limits to gate fidelities in that setup are related to experimental complications from finite lifetime and (re-)loading effects among others. Anomalous motional heating may eventually limit achievable gate fidelities, making it desirable to operate the setup at cryogenic temperatures. As far as trap and microwave near-field design is concerned, cryogenic operation will change the conductivity, dielectric loss and permittivity of the involved materials; all of these effects have been taken into account in the trap design. Figure 1 shows the trap geometry developed for initial trapping experiments, an adapted version of the geometry used in Refs. 18,19. Ions can be confined at a distance of $x = 70 \mu m$ from the surface using an RF potential applied to the conductor depicted in green; suitable potentials on electrodes DC$_1$–10 provide confinement along $\hat{y}$. The conductors shown in orange and red, when operated at a current near-resonant with an atomic transition, provide microwave near-fields suitable for multi- and single-qubit operations, respectively.

The apparatus described here was designed to house and cool such a trap down to below 10 K, provide XHV conditions, laser access from two orthogonal directions as well as electrical connections for DC and high frequency currents and voltages, and imaging of the trapped-ion resonance fluorescence. Furthermore, it is desirable to limit mechanical vibrations of the setup as much as possible, since stimulated-Raman laser beams impinging on the ion from different directions may be needed for ground state cooling, which would require phase coherence between the two beams. Figure 2 shows a false color picture of the entire system which will be discussed in this paper.

**FIG. 1.** Trap electrodes around the trap center (see main text). In the top left, a picture of the resonance fluorescence of three trapped $^9$Be$^+$ ions is shown. Points $\alpha$, $\beta$, $\gamma$ and $\delta$ are used for laser beam alignment (see section VIII). $B_0$ is the direction of the quantization axis, provided by a set of magnetic-field coils (see section VIII).

**FIG. 2.** Overview of the functional components of the system. a) cold-head with ultra-low vibration interface, b) outer vacuum chamber, c) radiation shield, d) inner vacuum chamber, e) imaging system, f) lower breadboard, g) optical table, h) upper breadboard, i) magnetic field coils, j) cold-head mount and translation stage.

1. **General cryostat design considerations**

The coldest part of a cryostat to which the experiment or sample is attached is called the cold finger. The design goal was to achieve between 3 and 10 K at the cold head, as further cooling typically only increases the complexity without significantly increasing the performance in the anticipated applications. An outer vacuum chamber shields the cold parts from ‘hot’ air to inhibit convective losses, air condensation and freezing on cold surfaces. An suitable isolation vacuum is typically below $10^{-4}$ mbar. A radiation shield between the outer vacuum chamber and the cold finger will shield the latter from ‘hot’ room temperature radiation. A typical radiation shield temperature would be between 30 K and 100 K. To take full advantage of the XHV conditions provided by a cryogenic environment, a self-sustaining, cold vacuum chamber containing the trap can be mounted to the cold finger. This inner vacuum chamber has no physical connection to the room temperature environment, except possible electrical lines. It has to be evacuated and sealed before cool-down.
2. Choosing the type of cooler

In the required temperature range, one generally has the choice between a closed and an open system cryostat design. An example of an open system is a bath cryostat, with reservoirs of liquid nitrogen at 77 K and liquid helium at 4.2 K attached to the radiation shield and cold finger respectively. Cooling power is only limited by the amount of cooling liquid that one can logistically master. Another open system is a flow cryostat in which the cooling liquids are continuously replenished from a reservoir. Both types of open systems boil off helium which can in part be recovered to lower overall costs. The constant need to refill a reservoir, the unpredictable costs due to changing helium prices and the lack of on-site available helium recovery systems led us to opt for a closed cycle system. Prominent types of closed systems are Gifford-McMahon (GM) coolers and pulse tubes. Both rely on highly pressurized helium of more than 10 bar as a coolant, provided by a compressor, and on cooling the cryogen against water or air. In both types, the helium is delivered to the so-called cold head to which the cold finger is attached. In the case of a GM cooler, the helium is used in a Sterling type cooling process that requires two moving pistons, one at room temperature and a cold one. The cold piston and the motor that drives it are located inside the cold head. The motor induces considerable vibrations at the cold finger on the order of 100 µm. In a pulse tube cooler, the helium is compressed by a piston outside the cold head. Therefore vibrations are two orders of magnitude lower than in a GM cooler. For an experiment that requires some level of interferometric stability, in our case at a wavelength of 313 nm, vibrations well below 100 nm are desirable. Both closed cycle systems do not provide these low vibration levels on their own. Different commercially available low vibration interfaces for both types of coolers claim to achieve comparable performance levels. Arguments to consider in system design are the typically lower initial cost of GM coolers. A GM cooler, however, requires more frequent maintenance because of abrasion of moving cold-head parts, approximately every 10000 h of operation vs. approximately every 20000 h for a pulse tube cooler. The normal maintenance procedure of a GM cooler can be done on-site while a pulse tube cooler often requires shipping to the manufacturer. To reduce potential down-times on the experiment because of cryo cooler maintenance, we opted for a GM cooler.

III. ELECTRICAL CONNECTIONS

A. Electrical requirements

Our application requires at least 2 high-frequency feed lines for microwave currents of about 1.08 GHz with a few Watts of peak power each, one for single-qubit operations and the other one for multi-qubit gates and interactions. To address different transitions in the hyperfine manifold, frequencies between 800 and 1500 MHz are needed. Even though we may not apply such high powers, we chose to design hardware that can support up to 50 W. We also require 1 line for an AC voltage of about 100 MHz with around 100 V amplitude connected to the RF electrode to ensure radial confinement of the ions. There are 10 DC electrodes in this trap, carrying voltages for axial confinement, micromotion compensation and other radial and axial positioning of the ions. One DC line has been included to carry up to 1 A of current for proper electrical grounding. We use an in-vacuum cryogenic Schwarzschild-type objective for ion- and trap-imaging. For ease of alignment and focusing, 3D positioning of the objective is highly desirable. Each axis requires a piezo driven translation stage and each stage requires 2 current-carrying lines, which brings the total number of DC current-carrying lines to 7. To be able to scale traps to a large number of ions (and electrodes) for applications in quantum logic and quantum simulations, we opted for a design with 8 high-frequency and 100 DC lines, 10 of which are able to carry a current of up to 1 A.

B. Electrical Design

1. DC connections

DC signals are generated by a fast arbitrary waveform generator. Before entering the outer chamber, each DC signal passes through a 0.3 MHz low pass filter (LPF-B0R3, Mini-Circuits). To connect trap electrodes (which only require voltages without currents), we use varnished constantan wire with an outer diameter of 0.224 mm (GVLZ175, GVL Cryoengineering). For grounding and all current carrying DC connections, we use electrolytic copper wire of outer diameter 0.28 mm (GVLZ175, GVL Cryoengineering). Without varnish the diameters are 0.193 mm and 0.25 mm respectively. Compared to copper, constantan has a fairly high electrical resistivity but low thermal conductivity. The thermal conductivity integral is defined as the heat conduction $\dot{q}_{\text{cond}}$ through a solid of uniform cross section $A$ and length $l$ between two temperatures $T_1$ and $T_2$ with a temperature-dependent thermal conductivity $\lambda(T)$:

$$\dot{q} = \frac{A}{l} \int_{T_1}^{T_2} \lambda(T) dT$$  \hspace{1cm} (1)

Ekin also provides these integrals between 4 K and temperatures up to 300 K for several materials. We used that data for constantan ($\lambda_{\text{const}}(T)$) but chose the analytical thermal conductivity model provided by NIST Cryogenic Technology Resources, Index of Material Properties for copper, the main reason being that it provides data for a few more different copper purities. We chose RRR=100 (Residual Resistance Ratio) as a reference as this comes closest to the used wire’s purity. With unitless temperature $\tilde{T} = T/K$, the NIST data gives:

$$\lambda_{\text{RRR}=100} = 10^{-2} \frac{2.2154 - 0.3806 \tilde{T}^0.5 - 0.295 \tilde{T} - 0.0483 \tilde{T}^1.5 - 0.0032 \tilde{T}^2}{1 - 0.4746 \tilde{T}^0.5 - 0.1387 \tilde{T} - 0.0483 \tilde{T}^1.5 - 0.0032 \tilde{T}^2} \frac{W}{m \cdot K} \hspace{1cm} (2)$$

Assuming an ambient temperature of 296 K, a radiation shield at 40 K and an inner chamber at 4 K, and also assuming perfect thermal anchoring of all wires at the respective temperature stages, with a wire-length of 160 mm between 296 K and...
40 K as well as 260 mm between 40 K and 4 K, we can calculate heat loads on both cold stages. One constantan wire produces a heat load of \( \approx 0.89 \text{ mW} \) on the 40 K stage and \( \approx 0.03 \text{ mW} \) on the 4 K stage. One copper wire leads to a heat load of \( \approx 49.1 \text{ mW} \) on the 40 K stage and \( \approx 13 \text{ mW} \) on the 4 K stage. All 90 constantan wires combined lead to an insignificant heat load of \( \approx 79.8 \text{ mW} \) on the 40 K stage and \( \approx 3.1 \text{ mW} \) on the 4 K stage. All 10 copper wires contribute \( \approx 491 \text{ mW} \) to the 40 K heat load and \( \approx 130 \text{ mW} \) to the 4 K heat load. The former can be easily absorbed by the more than 50 W available cooling power at 40 K but the latter consumes nearly 10% of the available cooling power of about 1.5 W at 4 K.

We have applied the DC lines in the following way: After cutting the wires to length, we removed the varnish by means of a motorized rotating blade wire stripper, with three quickly rotating blades with adjustable distance between them (ISOL-EX Typ 02, Fritz Diel GmbH & Co. KG). We assembled a 25-pin Sub-D UHV compatible cable to provide two copper and 23 constantan wires. We used materials supplied by Allectra GmbH. One female PEEK connector (212-PINF-25-S) was mounted on each end. We folded the tip of each wire once by 180°, so that the effective cross section doubled and crimped it into a small crimp pin (212-PINM-25-S). The wires were then wound 10 times around and glued onto a copper bobbin which was anchored to the 40 K stage. We used a thermally conductive two-component epoxy with low outgassing properties: the epoxy resin LOCTITE® STYCAST 2850FT together with the catalyst LOCTITE® CAT 24LV. The 160 mm long end was connected to a Sub-D feedthrough on a DN63CF flange at the outer chamber and the 260 mm long end was connected to a Sub-D feedthrough welded into a custom made flange at the inner chamber. The wiring between bobbin and inner chamber took place inside the radiation shield. A hole in the radiation shield, big enough for a 25 pin connector to pass through was later mostly covered with a copper sheet, leaving a hole only large enough for the wires, so room temperature thermal radiation would not pass through.

2. **High-frequency microwave current lines**

For microwave frequencies between 800 and 1500 MHz, coaxial cables are required to provide a well-defined impedance and shielding from noise sources. Standard SMA cables lead from DDS sources and amplifiers to the outer vacuum chamber. Floating SMA feedthroughs on a DN40CF flange guide the signal into the chamber. The connections between different temperature environments presents two apparently conflicting requirements - low thermal conductivity and high electrical conductivity. In most conductors, free electrons account for much of the heat transport, and they roughly follow the empirical Wiedemann-Franz law, whereby the ratio between thermal conductivity \( \kappa \) and electrical conductivity \( \sigma \) is proportional to the temperature \( T \). The proportionality constant \( L \), called Lorenz number, is approximately the same for most metals.

\[
\kappa / \sigma = LT
\]  

This leads to the observed behavior that if a metal is a good conductor for heat, it is also one for electricity. The same conclusion holds for geometrical concerns. The electrical conductance \( G \) of a wire depends on its cross section \( A \), length \( l \) and electrical conductivity \( \sigma \):

\[
G = \sigma A / l
\]

According to equation 1, a larger cross section of the transmission line will lead to higher heat transfer. The electrical conductance \( G \) also rises with larger cross section: Higher cross section of a conductor leads to more conduction of both, heat and electricity. Another source of heat is Joule heating. The dissipated power in a conductor is proportional to its resistance. This leads to conflicting requirements. In addition, for high frequency applications, one has to consider the impedance of all parts of the transmission line as sudden jumps in impedance lead to reflections and thereby a lower power at the ion trap. Interference effects inside the transmission line due to multiple reflections also have to be considered since there might be local current amplifications and therefore more local heat deposition. As an acceptable compromise between expected Joule-heating and low thermal conduction, we chose UT-141B-SS from Microstock. This is a semi-rigid coaxial cable with PTFE as a dielectric between a BeCu center and a 304 stainless steel outer conductor. It has no insulation on the outside. This makes thermal anchoring easier. On the down-side one has to take care of electrical insulation from the rest of the system to avoid ground-loops. According to the data sheet, the cable has an insertion loss of 0.83 dB/m at 1 GHz. With equation 1 and thermal conductivity data from NIST’s Cryogenic Technology Group, we calculated that, in an ideal case of perfect thermal anchoring on the 40 K stage, the heat load on the 4 K stage will be 3.4 mW due to thermal conduction. Figure 3 shows the thermal anchoring of the semi-rigid cable. For better outgassing performance, we removed silicone rubber gaskets from SMA connectors (Huber+Suhner, 11_SMA-50-3-15/111_N) and soldered them to both ends of the semi-rigid cable, using 315-LF-SOLDER-1M from Allectra as solder and Castolin 157 as flux. For better thermal contact, we applied Apiezon N grease to the cable and mounted it between two copper half-cylinders of 10 cm length. These were then mounted to the radiation shield with a 2 mm thick disk and a 22 mm long tube in between wire and shield. Both spacers are made out of Shapal because it is electrically isolating while still featuring a substantial thermal conductivity and it is also machinable with standard milling tools. We used a PTFE disk to electrically isolate screws from the radiation shield. We were not able to use this type of semi-rigid cable all the way from room temperature to 4 K. Flexible cable is required on the inside of the room temperature SMA feedthroughs because of the need to close the flange after attaching the cable. The semi-rigid cable is too stiff to support the required motion. Since the first cooling stage has ample cooling power, the main concern is the heat load on the second stage. We use a 25 cm long KAP50 cable from Allectra with SMA connectors on each end to connect the room temperature feedthroughs to the semi-rigid cable,
which runs only vertically inside the radiation shield. Connecting the semi-rigid cable to the inner chamber was also not easily achievable due to its stiffness. We use a 3 cm long KAP50S piece from Allectra with SMA connectors on both ends to connect the UT-141B-SS cable and the inner chamber. Floating SMA feedthroughs are used to guide the signal into the inner chamber. Inside the latter, a 10 cm long KAP50S piece with an SMA connector on one end and an MCX connector on the other end connects to the PCB to which the ion trap is bonded. All cables used up to this point have 50 $\Omega$ impedance. We measured the input return loss along the entire transmission line, including the PCB’s coplanar waveguide, bonding wires and the trap chip to be $-2.2 \pm 0.1$ dB at 1.083 GHz. This measurement has been carried out with a vector network analyzer (Rohde & Schwarz ZNB8) while the system was cooled down to 5 K. We have measured the insertion loss of all combined cables, leading to the PCB, at room temperature and at 1.083 GHz to be $-1.16$ dB. At lower temperatures this number should be smaller. Additionally including the coplanar waveguide, bonding wires and trap will increase it again. Since the current has to flow in and out of the trap, this number has to be roughly doubled, assuming mostly the same return path. This leads to the measured $-2.2$ dB or $39.5\%$ power dissipation. This is the only variable source of heating in our system. Adding up all static heat sources, DC lines, semi-rigid cables and thermal radiation, we reach a static thermal load of 165 mW. With a cooling power of about 1.5 W at 5 K, this leaves us with an acceptable power dissipation of 1.335 W, which leads, in the worst case scenario of all power being dissipated on the 4 K stage, to an acceptable average microwave input power of $\approx 3.4$ W. To verify this number, we set the temperature controller that is connected to the second stage to 5 K, and measured the amount of heating that it puts out versus the CW microwave power we applied to the sideband electrode at 1.084 GHz. We ramped up the output power of our microwave source until the temperature controller did not need to heat the system to keep it at 5 K. We then measured the microwave power with the a spectrum analyzer (Rohde & Schwarz FPC1000/FPC-B2) and a 40 dB attenuator (Mini-Circuits BW-N40W50+) to be $4.0 \pm 1.0$ W. This is in good agreement with the calculated value. For the implementation of multi-qubit gates, power would not be applied continuously, but only during gate operation. Assuming the parameters of $\tau$ (1122 $\mu$s pulse duration and $\approx 20$ ms wait time between square-envelope gate pulses), it would be possible to apply peak powers of $\approx 64$ W, to be compared to the 11 W used in Ref. before reaching cooling power limits.

3. Radio frequency trap drive

The surface-electrode Paul trap used here is operated at a radio frequency between 90 and 110 MHz for radial confinement of the ions. We use an HP 8640B oscillator to generate the desired rf frequency. A self-built helical resonator is mounted to the outside of the inner vacuum chamber and provides the required voltage step-up. We chose mostly the same type of cable configuration as for the microwave lines. The cable which, for the microwave lines, connects to the inner chamber, is attached to the resonator input in case of the rf signal. The resonator output is connected to the center pin of an SMA feedthrough with a bare wire, leading into the inner chamber, where a bare wire continues to connect it to the PCB to which the trap is bonded. The capacitive load of a coaxial line would pull the resonator frequency too much. Figure 4 shows an image of the rf resonator. Following design guides for helical coaxial resonators, we chose a compact cylindrical resonator of 42.1 mm height and 31 mm diameter with a resonance frequency of 100 MHz. The helix is made of 1 mm diameter OFE copper wire, has a pitch of 5.75 mm, diameter of 16 mm, height of 23 mm and is wound on a PTFE cylinder with a 0.5 mm deep helix-bevel for guidance. The signal is coupled in via an SMA feedthrough with a female connector on the inside. We removed the insulation from the tip of a varnish insulated 0.5 mm diameter copper wire with a rotating blade wire stripper (ISOL-EX Typ 02) and soldered a male SMA pin to it (solder: 315-LF-SOLDER-1M, Allectra). The latter is connected to the inner conductor of the SMA feedthrough and wound around the helix once, with the varnish touching the inner wall of the resonator housing. It is then guided through a 2 mm hole to the outside of the resonator housing and attached with an M2 screw. To make small adjustments to this incoupling wire, we loosen the screw, carefully push/pull the wire from the outside and tighten it again.

We determine the loaded Q-factor as follows: While everything is connected and cooled down to 5 K, we measure the reflected power or $S_{11}$ parameter vs frequency by connecting a Rohde&Schwarz ZNB8 Vector Network Analyzer to the appropriate room temperature SMA feedthrough. The resulting
FIG. 4. Cut out view of the rf-resonator (see text).

FIG. 5. Measurement of the resonator’s $S_{11}$ parameter, at 5 K, while connected to the ion trap. For clarity, only every 4th data point is plotted. The center frequency is at 99.37 MHz, the incoupling is $-8.05$ dB, the FWHM is 1.13 MHz, the Q-factor is 88.3. The resonance curve is shown in figure 5 and contains not only the frequency dependent behavior of the resonator but also of the feed-lines. The lines have an Ohmic loss and a frequency dependent damping, approximated to first order around the resonator’s resonance frequency. We model the resonator as a series RLC circuit ($Z_{\text{res}} = i\omega L + \frac{1}{i\omega C} + R$) attached to a transmission line with characteristic impedance $Z_0$ fed from a source with the same impedance $Z_0$. The voltage reflection coefficient is given by $\Gamma = \frac{Z_{\text{in}} - Z_0}{Z_{\text{in}} + Z_0}$, and the power reflection coefficient by $|\Gamma|^2 = S_{11}$. We find

$$S_{11}(\omega) = 10\log_{10} \left( \frac{(\gamma - \gamma_s)^2 \omega^2 + (\omega^2 - \omega_0^2)^2}{(\gamma + \gamma_s)^2 \omega^2 + (\omega^2 - \omega_0^2)^2} \right) - \Omega \omega - R_0$$

where an additional term has been included for the frequency dependent attenuation of the line between the resonator and point of the return power measurement. $R_0$ the Ohmic loss of the feed-lines and $\Omega$ the first-order frequency dependent loss coefficient of the feed lines. Here, $\gamma = \frac{1}{\tau}$ determines the frequency width with of the unloaded resonator, $\gamma_s = \frac{1}{\tau_s}$ is related to the source and line impedance and $\omega_0 = \frac{1}{\sqrt{LC}}$ is the resonance frequency. Using a nonlinear least-squares fit to the data (see Fig. 5), we find $\gamma_s = 2\pi \cdot 0.34$ MHz, $\gamma = 2\pi \cdot 0.79$ MHz, and $\omega_0 = 2\pi \cdot 99.37$ MHz. The Q-factor is the ratio between resonance frequency and full width at half maximum (FWHM), using the feed-line damping $-\Omega \omega - R_0$ as reference level.

$$Q = \frac{\omega_0}{\text{FWHM}} = \frac{\omega_0}{\gamma + \gamma_s}$$

Note that because of losses on the feed-lines and imperfect coupling, the FWHM cannot be extracted from the distance between the -3dB points of the signal. We currently run the resonator at +23 dBm input power. The incoupling is at $-8.05$ dB, the Q-factor is 88.3. We continuously monitor input and reflected power with a bidirectional coupler (Mini-Circuits ZFBD20-62HP-S+) and two power detectors (Mini-Circuits ZX47-20LN-S+), hooked up to an Arduino Nano with an LC display. In case of resonance frequency drifts, we adjust the HP 8640B output frequency and observe the monitoring device to minimize reflections.

IV. VACUUM SYSTEM

Designing vacuum systems for room temperature UHV operation requires carefully choosing materials with respect to outgassing performance and maximum baking temperature. For cryogenic vacuum systems, these requirements can be relaxed. A vacuum chamber that reaches only a moderate vacuum of about $10^{-6}$ mbar at room temperature can, when properly cooled down, reach XHV conditions.

A. Outer chamber: isolation vacuum

The outer vacuum chamber has been designed to fulfill all requirements for UHV operation, but has not been baked yet because it only serves as an isolation vacuum for the self-contained inner chamber. We use CF-flanges at every connection and currently rely on Viton® gaskets at ports that needed to be opened for trap exchanges. Annealed copper gaskets are used for seals on all other ports. The list of materials in the outer chamber is: OFE-copper, beryllium-copper, stainless steel, PTFE, gold-plated bronze, constantan, PEEK, Kapton, Stycast 2850FT as well as fused silica.
glass and optical coatings for various wavelengths on viewports. This material selection ensures that the chamber could support lower pressures, if the need arises. After assembling and cleaning, the chamber is evacuated with a turbo molecular pump (Pfeiffer TMU 521) connected to a backing scroll pump (Edwards, nXDS 10i). We monitor the pressure with an active Pirani/cold cathode gauge (Pfeiffer PKR 251). After about 5 h, it reaches $10^{-6}$ mbar and we turn on the cryocooler. When the temperature reaches 5 K after about 10 h, the isolation vacuum reaches less than $3 \times 10^{-8}$ mbar and we close the valve (VAT, 54132-GE02) connecting chamber and turbopump. The vacuum is then sustained at the low $10^{-8}$ level by the cryo-pumping effect. For support, we have mounted two ion combination pumps (SAES, NEXTor D 100-5) to the outer chamber, which are currently not in use. During test runs, without baking, we have measured pressures in the upper $10^{-10}$ mbar range while these pumps were active. The outer chamber is mainly made out of non-magnetic stainless steel (1.4429 or 316LN). The only magnetizable parts inside the whole apparatus are the ≈0.3 mm thin, 304 stainless steel, outer conductors of the high frequency lines. These were not available in 316LN and the advantages of thermal and electrical characteristics outweigh the magnetic influence as these lines are at least 95 mm away from the ions.

B. Inner chamber: 4 K ion trap housing

The inner chamber is a self-contained vacuum chamber, made predominantly from oxygen-free (OFE) copper and non-magnetic stainless steel (316LN or 1.4429). It has a quadratic $140 \times 140 \text{mm}^2$ footprint and a height of 160 mm. The OFE copper supporting structure consists of two 25 mm thick top and bottom lids as well as a 15 mm wall thickness enclosing body. Structurally, it would have been possible to use thinner materials, which would have the advantage of lower heat capacity and therefore faster cooldown. However, a higher heat capacity acts as a low pass filter for thermal fluctuations. Thick walls also provide better shielding from outside electric and magnetic noise. Figure 6 shows an image of three sides of the inner chamber. The inner chamber’s body has holes and pockets to house stainless steel flanges which contain welded-in electrical feedthroughs as well as CF16 compatible flute interfaces and spaces for 20 mm diameter indium sealed viewports. The bottom lid houses two indium sealed stainless steel adapters that have CF16 interfaces. The top lid only has 4 M4 threads to mount it to the second cooling stage. The RF resonator is mounted to one of the side walls. We use custom stainless steel flanges as a convenient multi-purpose adapter. Standard CF components rely on two opposing steel knife edges with a softer seal in between, which is not reusable. Common UHV compatible electrical feedthroughs also come in stainless steel packages which cannot be easily welded into OFE copper. Therefore we required some reusable copper to steel interface. We use a 1 mm thick indium wire between the inner chamber wall and the flange to make a vacuum tight seal. We use anti-reflection coated CF16 viewports for 313 nm for the imaging laser ports. For the 235 nm ionization and the 1064 nm ablation beams, as they are traveling parallel to each other, 6 mm apart, we use 20 mm diameter uncoated fused silica disks which were indium-sealed to the adapter flange for both beams. An image of the chamber’s inside is shown in fig. 6 with the wiring left out for clarity. The inside dimensions are $110 \times 110 \times 107 \text{mm}^3$. At the center, there is a copper block of $49 \times 49 \times 7.9 \text{mm}^3$, connected with a series of mechanical adapters to the base plate attached to the cold finger. At the center of this copper block is a 1.63 mm tall plate with a surface area of $\approx 4.8 \times 4.8 \text{mm}^2$. An ion trap chip of the same area (sapphire substrate, thickness 635 µm) is glued to the plate. A 1.524 mm thick printed circuit board (PCB), made out of gold coated Rogers 4350B (CONTAG AG) with a 5 × 5 mm hole surrounds the trap and is bolted onto the mounting block (‘filter board’). The PCB houses one 25 pin Sub-D connector for DC signals and grounding as well as four MCX connectors for RF and microwave signals. The DC lines pass an RC lowpass (1 kΩ Anaren R1A15081001J3A0 and 820 pF Novacap 0603N821J101P), the microwave signals are guided towards the trap with a 50 Ω co-planar waveguide. We left a 1.05 mm gap between ground-plane and the 0.4 mm wide rf-line to minimize capacitive load on the resonator. Wire bonds establish connections between filter board and ion trap for all electrical connections. A Faraday cage with ports for laser beams and at least 1 mm away from electrical lines surrounds the ion trap. It has an opening for imaging light to
pass through, which is covered with a gold mesh (Precision Ef
erforming MG17) to keep a defined ground potential above the trap. The Faraday-cage structure also houses a 0.5 mm diameter beryllium wire, located 13 mm away from the trap center. An opening of 2.4 mm diameter gives way for the ablation laser to hit the Be wire. Another opening of 1.4 mm diameter pointing from the wire to the trap center acts as a guide for ablated Be atoms to reach the trap. Since the Be ablation plume expands in nearly every direction, the 1.4 mm hole also acts as an aperture, minimizing Be contamination of the chip. A Schwarzschild objective is placed 8 mm above the trap. It is mounted on a 3D translation stage made out of a stack of two x-nanopositioners (SLC-1720-CR-UHVT-NM-TI, SmarAct GmbH) and one z-nanopositioner (ANPz101, a
cube systems AG), all fully non-magnetic. The six current carrying lines needed to connect the translation stage, are con
tected to one of the 25 pin Sub-D ports of the inner chamber (not the one used for trap voltages). On the z-positioner, we
connected to one of the 25 pin Sub-D ports of the inner chamber
carrying lines needed to connect the translation stage, are con
tected to one of the 25 pin Sub-D ports of the inner chamber

FIG. 7. Upside-down view of the inner chamber’s inside compo
ents. Electrical wiring is left out for clarity. Wires connect the lower side of the filter board to feedthroughs in the walls (not shown either).
pressure $P_{H_2} = 1.2 \times 10^{-12} \text{ mbar}$ at a confidence level of 68% and $P_{H_2} = 2.5 \times 10^{-12} \text{ mbar}$ at CL=90%.

V. VIBRATION ISOLATION

A. Design

Mechanical vibrations due to the closed-cycle cryocooler are of concern because of a potential relative movement between laser beams and ions. This is particularly relevant to ensure phase stability of two Raman laser beams for controlling the ions and to a certain extent for keeping the laser intensity at the ions’ position stable over time. In a typical room-temperature setup, a vacuum chamber would be mounted on top of an optical table which also carries the relevant laser systems. Usually, there are no moving parts on the table. In section II A 2, we discussed why a GM cooler was chosen for the present setup. The cold-head of a GM cooler contains a motor which induces significant vibrations, on the order of $100 \mu\text{m}$ at the cold finger to which the experiment is attached. In the present system, shown in figure 8, the Sumitomo RDK-415D cold head is decoupled from the rest of the experimental setup with a buffer gas vibration isolation system manufactured by ColdEdge Technologies. The vibrating part is not mounted to the optical table, on which the ion trap and lasers are mounted, but attached to the ceiling. The cold finger is fitted into a tube with a helium exchange gas which transmits the cooling power without the vibrations. Rubber bellows on top of this tube constrain the helium and are the only mechanical connections between the vibrating cold-head and the gas-filled tube. At the bottom of the tube, helium is at the cold finger temperature, while at the top it is at room-temperature. Some helium leaks through the bellows; it is therefore constantly replenished. We reduce the pressure of a 50 l and 200 bar cylinder of 99.999% pure helium using two stages of pressure regulators to about 30 mbar above ambient pressure and feed the gas into the top end of the exchange gas tube. The overpressure keeps non-helium gases out, especially during cool down as the gas is contracting. While the cryocooler is running, the consumption is about 3 cylinders per year. The exchange-gas tube is part of the outer vacuum chamber, which is mounted on the optical table. In the middle of the tube, where the first cooling stage of the GM cooler is located, we mount the radiation shield. At the tube’s bottom, we connect the inner vacuum chamber. On both temperature stages, the vibration isolation works as follows: concentric copper cylinders a few cm long and about 5 mm thick are connected to the cold finger. In the gaps between the cylinders, similar concentric copper cylinders are mounted to the exchange-gas tube. There is a gap of about 0.5 mm between these matching pairs of cylinders. One has to ensure that the rings do not touch, as this would enable the direct transmission of mechanical vibrations. The cold-head therefore has to be aligned relative to the exchange-gas tube with better than 0.5 mm accuracy. We have built an alignment platform, mounted to the ceiling, on which the cold-head rests, that has a three point mount on an x-y-translation stage to align the cold-head relative to the optical table. Figure 9 shows the alignment platform. To minimize vibrations coupling in from the floor, the optical table is supported by pneumatic legs outfitted with repositioning valves with a positioning accuracy of better than 0.3 mm (86-19888-02, TMC) so that, after movement, the optical table comes back to a position in which the vibration isolation does not need to be realigned. In principle, it should be possible to check for electrical contact between the cold-head and the outer vacuum chamber to ensure that the copper cylinders do not touch. In reality, metallic helium lines and electrical cables are connected to the cold head, which, via the helium compressor, are grounded, like the optical table. Checking for electrical contact is therefore only reliable...
A Michelson-type interferometer has been built to characterize the residual vibrations of the inner vacuum chamber relative to the optical table. The interferometer uses 626 nm light from the sum frequency generation setup (see section VI). The 1050 nm and 1550 nm lasers have a specified short-term linewidth of less than 10 kHz and less than 1 kHz, respectively. The probe mirror is mounted to the inner chamber, while the reference mirror is on the optical table, supported by a piezo actuator. The arm-lengths were equal to within 5 cm. For the measurement of movement parallel to the optical table, we placed the interferometer on a breadboard surrounding the outer chamber (h in figure 2). For a second measurement, along the direction of gravity, we placed it on a smaller breadboard below the optical table, usually reserved for ion imaging optics and camera (f in figure 2).

We detected the signal on one port of a differential photodetector (2007 Nirvana, Newport). The second port was illuminated with laser light that was split off from the laser source before entering the interferometer. We adjusted the respective power levels to obtain a signal centered around 0 V. We locked the signal to the zero-crossing with a PID controller (PID 110, Toptica) by acting on the piezo actuator, therefore forcing the corresponding mirror to exhibit the same movement as the probe mirror. We recorded the piezo voltage on an oscilloscope (HMO 3524, Hameg) and calculated the corresponding travel distance. The voltage to distance relation of the piezo was calibrated by replacing the probe mirror with a mirror on the optical table and scanning over four fringes. We measured vibrations at different temperatures around the boiling point of helium. At temperatures where the exchange gas is in fact liquid, vibration amplitudes of about 50 nm in the vertical direction and about 1.5 µm in the horizontal direction were observed. When the helium is gaseous, we measured vibration amplitudes of 51 nm (13.5 nm rms) in the horizontal and 29 nm (7.8 nm rms) in the vertical direction.

B. Characterization

A Michelson-type interferometer has been built to characterize the residual vibrations of the inner vacuum chamber relative to the optical table. The interferometer uses 626 nm light from the sum frequency generation setup (see section VI). The 1050 nm and 1550 nm lasers have a specified short-term linewidth of less than 10 kHz and less than 1 kHz, respectively. The probe mirror is mounted to the inner chamber, while the reference mirror is on the optical table, supported by a piezo actuator. The arm-lengths were equal to within 5 cm. For the measurement of movement parallel to the optical table, we placed the interferometer on a breadboard surrounding the outer chamber (h in figure 2). For a second measurement, along the direction of gravity, we placed it on a smaller breadboard below the optical table, usually reserved for ion imaging optics and camera (f in figure 2).

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For comparison, consider the system described in [22] based on a cryogenic ion trap mounted to a GM cooler, mechanically decoupled via an exchange gas, comparable to our system. Relative to the time series of vertical vibrations in figure 10(a) to figure 7(c) of reference [22], our vibration amplitudes are roughly a factor of two smaller. Comparing the horizontal rms spectra of figure 10(j), obtained with a resolution bandwidth (RBW) of 0.167 Hz with the 7.7 K measurement of figure 7(a) of reference [22]; obtained with a RBW of 0.1 Hz, our dominant rms values are about a factor of 7 lower. Now consider the custom vibration isolation for a pulse tube cooler described in reference [33]. Comparing the vertical rms spectra of figure 10(c) to figure 13(f) of reference [33], obtained with a RBW of 0.1 Hz, our system shows more than one order of magnitude lower vibration amplitudes. Comparing the horizontal rms spectra of figure 10(j) to figure 13(d), our results show the same order of magnitude, with ref. [33] performing slightly better at some frequencies. Reference [34] describes an alternative approach based on a flow cryostat. Comparing horizontal time series and rms spectra of figure 10(f) and j) with corresponding graphs in figure 5 of reference [34], our system has only twice the time-series amplitude and comparable amplitudes in the rms spectrum relative to this system that does not have any moving parts at all close to the trap. Reference [34] does not show data for vertical vibrations.
FIG. 10. Vertical and horizontal vibration time series, resulting power density spectra (PSD) and vibration amplitude spectra. a) Time series for vertical vibrations at 5 K. b) Comparison of PSD spectra for different second stage temperatures and the case of a shut-off cold-head. Cooling was shut off at 5 K and the measurement was taken about 1 min afterwards. The peak at around 40 Hz is the eigenfrequency of the upper breadboard (see h in figure 2) surrounding the vacuum chamber. The peak at around 100 Hz is the eigenfrequency of the lower breadboard (see f in figure 2). For this measurement, the interferometer was placed on the lower breadboard. We attribute prominent features between 100 Hz and 200 Hz to vibrations either of or inside the gas exchange tube. Changing equilibrium vapor pressures for different helium temperatures lead to different amounts of liquid helium present in the tube. These different helium levels are sloshing around in the tube at different frequencies. c) Same as b) but showing only data for 4.5 K and above, where no liquid helium is present. d) Comparison of vibration amplitude rms spectra for different second stage temperatures and the case of shut-off cold-head. Data from b) converted to rms with a resolution bandwidth of 0.167 Hz. e) Same as d) but showing only data for 4.5 K and above, where no liquid helium is present. f) Time series of horizontal vibrations at 6 K. We attribute the presence of the signals, recurring at about 1 s intervals, not to a failure or misalignment of the ultra-low vibration interface but to acoustic excitation of the upper breadboard by the sounds emitted by the cold-head operating at a rate of about 1 Hz. A more rigid breadboard can be desirable in the future. Early measurements have shown one order of magnitude larger displacements which were reduced to the present level by adding more mechanical connections or posts between the upper breadboard and the optical table. g) Horizontal PSD spectra for 3.1 K and 6 K. The prominent peak is at the eigenfrequency of the upper breadboard surrounding the vacuum chamber (see h in figure 2), on which the interferometer is placed. Harmonics are present at around 80 Hz and 120 Hz. h) Same as g) but only at 6 K. i) Horizontal vibration amplitude rms spectra for 3.1 K and 6 K. Data from g) converted to rms with a resolution bandwidth of 0.167 Hz. j) Same as i) but only at 6 K.
VI. LASER SYSTEMS

For Doppler cooling, we use light at 313 nm, generated by sum frequency generation of two infrared lasers to the visible with subsequent frequency doubling to the UV.\(^{[36]}\) We combine 5 W of a 1550 nm and 2.5 W of a 1050 nm laser, both fiber lasers (ADJUSTIK, NKT Photonics) with subsequent fiber amplifiers (BOOSTIK, NKT Photonics) inside a PPLN crystal to reach about 1 W of 626 nm light. We stabilize the frequency to an iodine line in a Doppler-free saturated absorption spectroscopy setup. We use a non-linear BBO crystal inside a bow-tie cavity to double the laser frequency and reach about 100 mW of 313 nm light. Using two 50/50 beam splitters, the light is delivered to three AOM (acousto-optic modulator) setups for switching and frequency shifting. One AOM shifts the light by -100 MHz for far-detuned Doppler cooling. Another beam is shifted by +624 MHz in a double-pass AOM setup for near-detuned Doppler cooling and detection. A third beam also passes a double-pass AOM and is shifted by -634 MHz. All beams are combined again and coupled into a photonic crystal fiber before passing through polarization optics and being focused into the vacuum chamber. The -634 MHz detuned beam is used for repumping during cooling and state preparation sequences. Since this repumper is used only during an experimental sequence and the far-detuned Doppler beam is only used during loading, these beams are never on at the same time. We decided to circumvent the power loss in the 1st order of the far-detuned Doppler beam by feeding the repumper through the 100 MHz AOM and overlapping its 0th order of diffraction with the 1st order of the far-detuned Doppler beam.

For production of neutral beryllium atoms, we send a 5 ns pulse of a 1064 nm laser onto a beryllium wire. The laser is a Q-switched Nd:YAG laser with a pulse energy of 28 mJ and variable repetition rate of 1-15 Hz (Minilite I, Continuum). We ionize neutral beryllium via a two-photon process.\(^{[33]}\) A diode-seeded tapered amplifier (TA pro, Toptica) that runs at 940 nm is frequency-doubled in a PPKTP crystal inside a bow-tie cavity to 470 nm. In a second frequency doubling cavity with a BBO crystal, 235 nm light is generated. We start with 1 W in the infrared and end up with 12 mW in the UV, of which we use about 1.5 mW for ionization.

VII. IMAGING SYSTEM

We collect the fluorescence of the beryllium ions with an in-vacuum Schwarzschild-type objective. An intermediate image appears just below the outer vacuum chamber, about 1.5 cm below the optical table’s top surface. In the intermediate image plane, a motorized four-blade aperture can be used to cut off stray light. The intermediate image is transferred to the detectors by a combination of two lenses. Moving the lenses along an optical rail, we can choose magnification factors between 10 and 95. With a motorized flip mirror the light can be sent either to a photomultiplier tube (Hamamatsu H10682-210) or to an EMCCD camera (Andor iXon Ultra DU-888).

VIII. TRAP LOADING

For loading, we apply appropriate voltages on all trap electrodes that are required to establish a confining potential. Magnetic field coils (see \(^{[8]}\)) provide a quantization field of 22.3 mT at the trap center, at an angle of 70° with respect to the axial trap direction (see \(B_0\) in figure \(^{[1]}\)). We switch on the 235 nm and both Doppler beams of the 313 nm laser, all aligned through the trap center. Then we shoot one 9.3 mJ pulse of the 1064 nm laser onto a 0.5 mm diameter beryllium wire, located about 13 mm away from the trap center. Neutral beryllium is ablated and forms a gas jet directed towards the trap center. Atoms with low kinetic energy are ionized by 1.5 mW of the 235 nm laser, cooled by 300 \(\mu\)W of the far-detuned and 10 \(\mu\)W of the near detuned 313 nm laser and trapped in the potential as shown in the inset of figure \(^{[1]}\). Aligning the 313 nm and 235 nm beams is done by moving the objective to image the edge of the trap-chip. We hit the chip side with a laser beam. Once we see it on the camera we align it further to obtain a maximally broad reflection on the chip’s surface. We then move the objective along known geometric features like gaps between chip electrodes and follow with the laser beam. The trap center can be geometrically identified as the center between an imagined line between two known features (points \(\alpha\) and \(\beta\) in figure \(^{[1]}\)). We align the 313 nm beam such that it hits points \(\alpha\) and \(\beta\), thereby ensuring that it also passes through the trap center. We do the same for the 235 nm beam by using points \(\gamma\) and \(\delta\). We align the beams parallel to the chip surface and subsequently pull them away from the surface by 70 \(\mu\)m, as this is the surface to trap center distance. We then also move the objective by the same distance, so that it images the trap center. We align the ablation laser on the beryllium wire, so that as many ablated neutral atoms as possible fly through the trap center. The ablation laser enters through the same windows as the ionization beam, 6 mm apart from and parallel to it. We observe the beryllium wire by having a camera positioned on the opposite side behind the exit windows. We operate the laser in low power mode and move the beam around until we can confirm with the camera that it hits the wire. Light is reflected by the wire, some of it in the direction of the chip. Some of the light hitting the chip is then reflected into the imaging system and eventually ends up at the EMCCD camera, where it looks like a large bright circle. We have observed that if we move the ablation beam around to maximize the amount of light detected by the EMCCD camera, we also maximize the probability of neutral atoms reaching the trap center. An explanation for this is that the shape of an ablation plume is a semi-ellipsoid, with the major axis pointing out of the ablated surface, perpendicular to it. In the same direction, the majority of atoms are ejected.\(^{[38]}\) Diffuse scattering follows Lambert’s cosine law, with the most light scattered perpendicular to the scattering surface. The directions of most ejected atoms and most scattered light coincide, making light collection in the imaging system a valid tool to optimize the ablation beam position.
IX. CONCLUSION

We have designed and commissioned an ultra-low vibration closed-cycle cryogenic ion trap setup for surface-electrode ion traps. Vibration amplitudes at the noise level of a Michelson interferometer were found. Residual vibrations in the horizontal direction can be further suppressed using a more rigid optics platform. With order 100 lines for DC control voltages, eight rf and microwave lines and optical access along 2 orthogonal directions, the system will allow the implementation of a small-scale quantum processor or simulator with trapped ions based on microwave near-field control.

DATA AVAILABILITY STATEMENT

The data that support the findings of this study are available from the corresponding author upon reasonable request.

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